



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

re Patent Application of )  
Shunpei YAMAZAKI et al. )  
Serial No. 09/255,777 )  
Filed: February 23, 1999 )  
For: SEMICONDUCTOR DEVICE AND )  
METHOD FOR FORMING THE SAME )

Art Unit: 2812  
Examiner: R. Booth

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AMENDMENT

Commissioner for Patents  
Washington, D.C. 20231

Sir:

Responsive to the Office Action dated **February 6, 2001**, the period for response having been extended one (1) month to June 6, 2001, the following amendments and remarks are submitted in connection with the above-identified application.

IN THE CLAIMS:

Please cancel claims 1-11, 44, 45 and 62-64 without prejudice or disclaimer to the subject matter recited therein.

Please amend claims 12, 18, 23, 29, 34, 37, 41, 53, 55 and 58 as follows. Attached hereto is a marked-up copy of the amended claims.

*Subj*  
steps of:  
12. (Amended) A method for fabricating a semiconductor device, comprising the steps of:  
    forming a semiconductor film comprising amorphous silicon on an insulating surface;  
    forming an insulating film on said semiconductor film;  
    introducing boron into at least a portion of said semiconductor film through said